



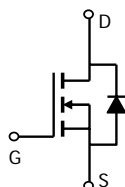
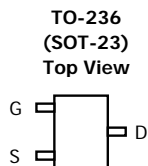
## AO3400, AO3400L ( Green Product ) N-Channel Enhancement Mode Field Effect Transistor

### General Description

The AO3400 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. AO3400L ( Green Product ) is offered in a lead-free package.

### Features

$V_{DS}$  (V) = 30V  
 $I_D$  = 5.8 A  
 $R_{DS(ON)} < 28m\Omega$  ( $V_{GS} = 10V$ )  
 $R_{DS(ON)} < 33m\Omega$  ( $V_{GS} = 4.5V$ )  
 $R_{DS(ON)} < 52m\Omega$  ( $V_{GS} = 2.5V$ )



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>A</sup>	$I_D$	5.8	A
$T_A=25^\circ\text{C}$			
Current <sup>A</sup>		4.9	
$T_A=70^\circ\text{C}$			
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	30	
Power Dissipation <sup>A</sup>	$P_D$	1.4	W
$T_A=25^\circ\text{C}$			
$T_A=70^\circ\text{C}$		1	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	65	90	$^\circ\text{C/W}$
$t \leq 10s$				
Maximum Junction-to-Ambient <sup>A</sup>		85	125	$^\circ\text{C/W}$
Steady-State				
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	43	60	$^\circ\text{C/W}$
Steady-State				

Electrical Characteristics ( $T_J=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	30			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^{\circ}\text{C}$			1 5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 12\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	0.7	1.1	1.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$ , $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$ , $I_D=5.8\text{A}$ $T_J=125^{\circ}\text{C}$		22.8 32	28 39	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$ , $I_D=5\text{A}$		27.3	33	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$ , $I_D=4\text{A}$		43.3	52	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=5\text{A}$	10	15		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$ , $V_{GS}=0\text{V}$		0.71	1	V
$I_S$	Maximum Body-Diode Continuous Current				2.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=15\text{V}$ , $f=1\text{MHz}$		823	1030	pF
$C_{oss}$	Output Capacitance			99		pF
$C_{rss}$	Reverse Transfer Capacitance			77		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		1.2	3.6	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=4.5\text{V}$ , $V_{DS}=15\text{V}$ , $I_D=5.8\text{A}$		9.7	12	nC
$Q_{gs}$	Gate Source Charge			1.6		nC
$Q_{gd}$	Gate Drain Charge			3.1		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$ , $V_{DS}=15\text{V}$ , $R_L=2.7\Omega$ , $R_{GEN}=3\Omega$		3.3	5	ns
$t_r$	Turn-On Rise Time			4.8	7	ns
$t_{D(off)}$	Turn-Off DelayTime			26.3	40	ns
$t_f$	Turn-Off Fall Time			4.1	6	ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		16	20	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=5\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		8.9	12	nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The value in any a given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80 $\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

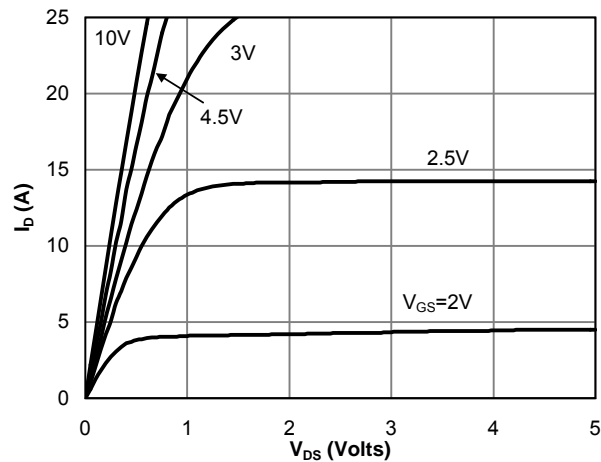


Fig 1: On-Region Characteristics

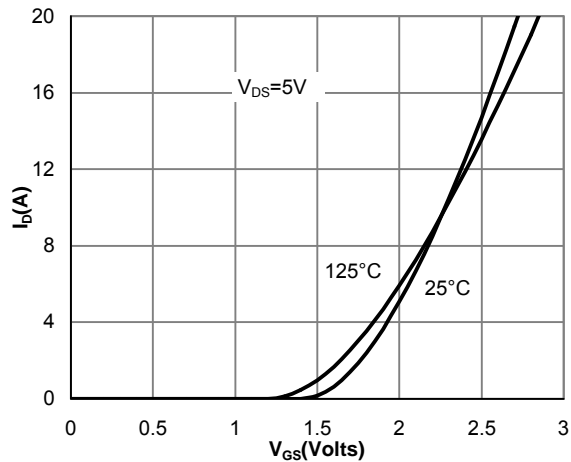


Figure 2: Transfer Characteristics

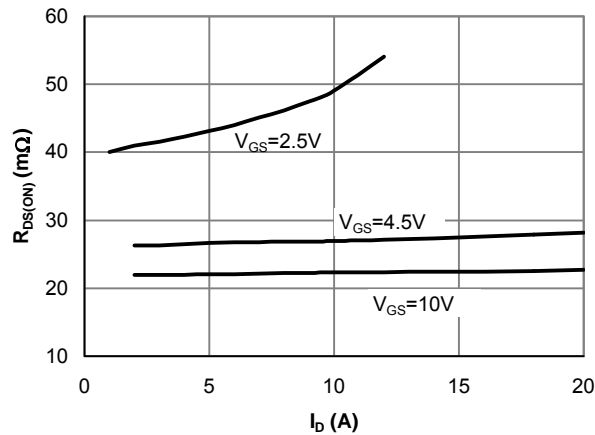


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

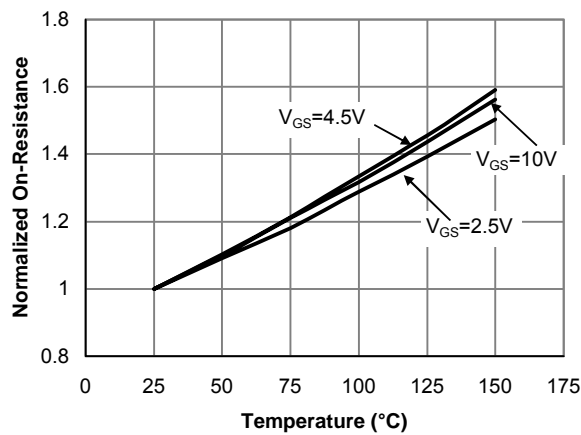


Figure 4: On-Resistance vs. Junction Temperature

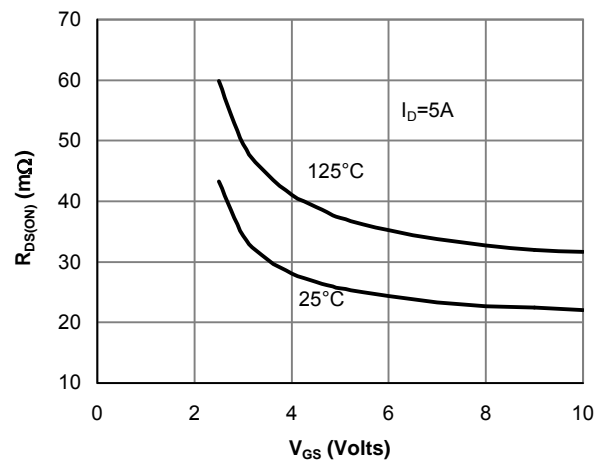


Figure 5: On-Resistance vs. Gate-Source Voltage

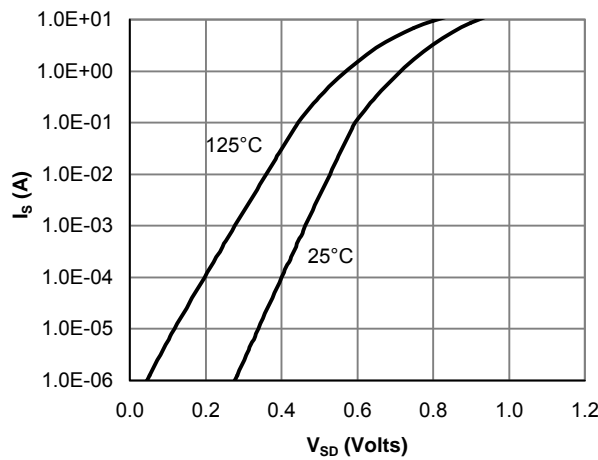


Figure 6: Body-Diode Characteristics

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

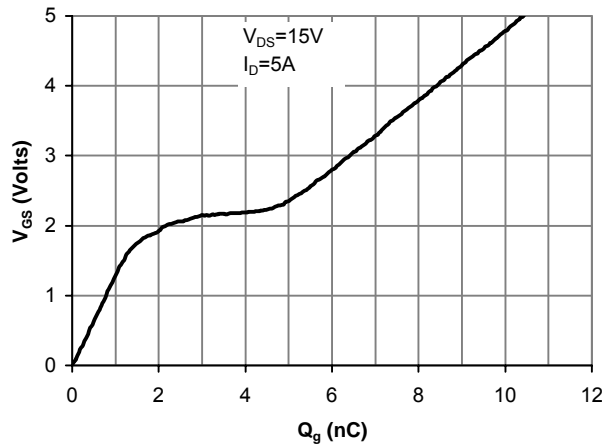


Figure 7: Gate-Charge Characteristics

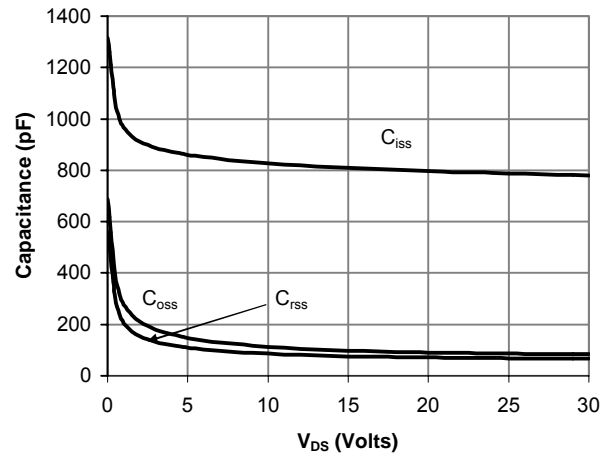


Figure 8: Capacitance Characteristics

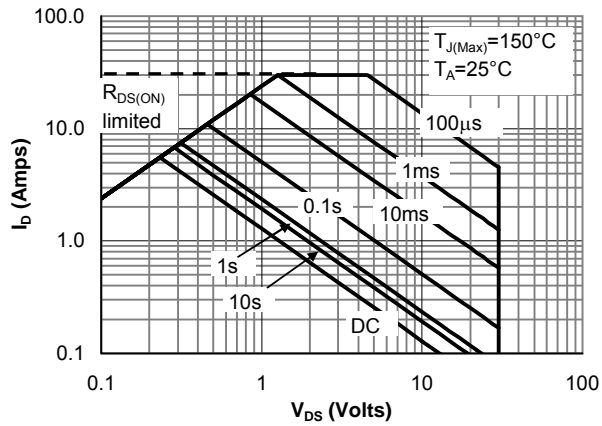


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

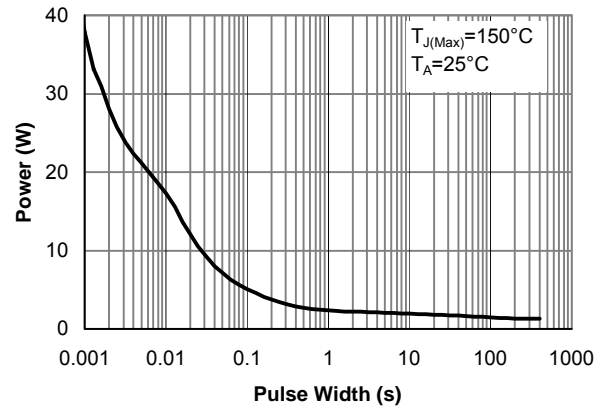


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

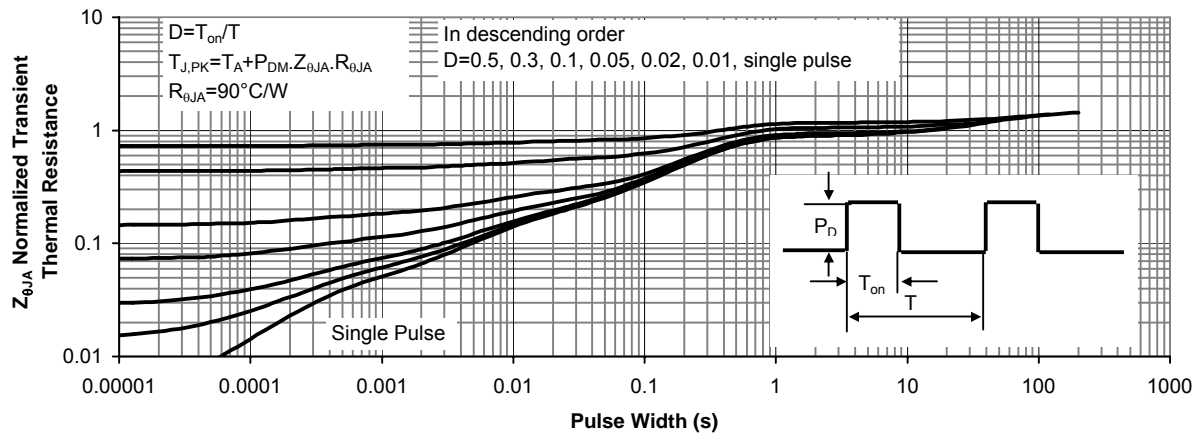


Figure 11: Normalized Maximum Transient Thermal Impedance